



ZXMN7A11GQ

Product Summary

BV _{DSS}	R _{DS(on)} Max	Ι _D T _A = +25°C
70V	0.13Ω @ V _{GS} = 10V	3.8A

Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control
- Class-D audio output stages

70V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZXMN7A11GQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

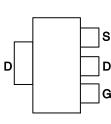
Mechanical Data

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

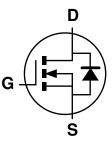


SOT223 (Type DN)

Top View



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Package	Packing		
Fait Nulliber	compliance	Fackage	Qty.	Carrier	
ZXMN7A11GQTA	Automotive	SOT223 (Type DN)	1,000	Tape & Reel	
ZXMN7A11GQTC	Automotive	SOT223 (Type DN)	4,000	Tape & Reel	

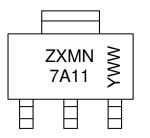
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



ZXMN 7A11 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 2= 2022) WW or \overline{WW} = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	70	V	
Gate-Source Voltage	V _G	±20	V	
Continuous Drain Current, V _{GS} = 10V	$T_A = +25^{\circ}C$ (Note 6) $T_A = +70^{\circ}C$ (Note 6) $T_A = +25^{\circ}C$ (Note 5)	ID	3.8 3.0 2.7	A
Maximum Continuous Body Diode Forward Current (Note 6)		ls	3.8	A
Pulsed Drain Current	I _{DM}	10	А	
Pulsed Source Current (Body Diode)	I _{SM}	10	А	

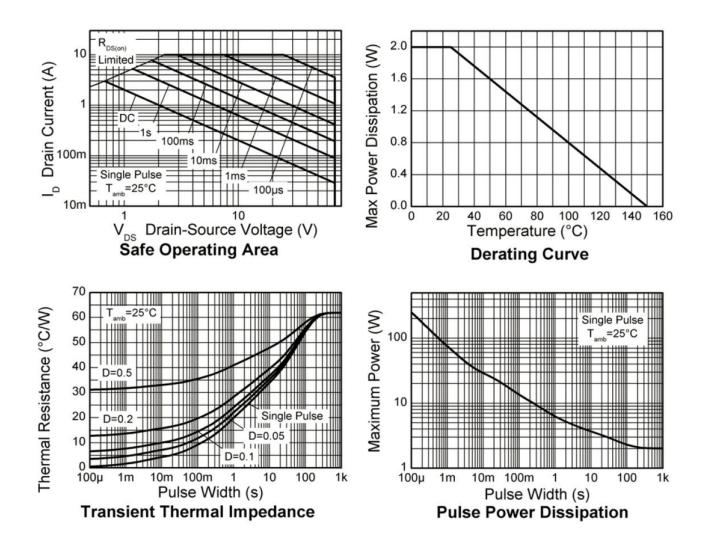
Thermal Resistance (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
total Power Dissipation at $T_A = +25^{\circ}C$ (Note 5)		2.0	W
Linear Derating Factor (Note 5)	PD	16	mW/°C
Total Power Dissipation at $T_A = +25^{\circ}C$ (Note 6)	n at TA = +25°C (Note 6)		W
Linear Derating Factor (Note 6)	PD	31	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R ₀ JA	32	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes: 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. For a device surface mounted on FR-4 PCB measured at $t \le 5$ sec.



Thermal Characteristics (@TA = +25°C, unless otherwise specified.)





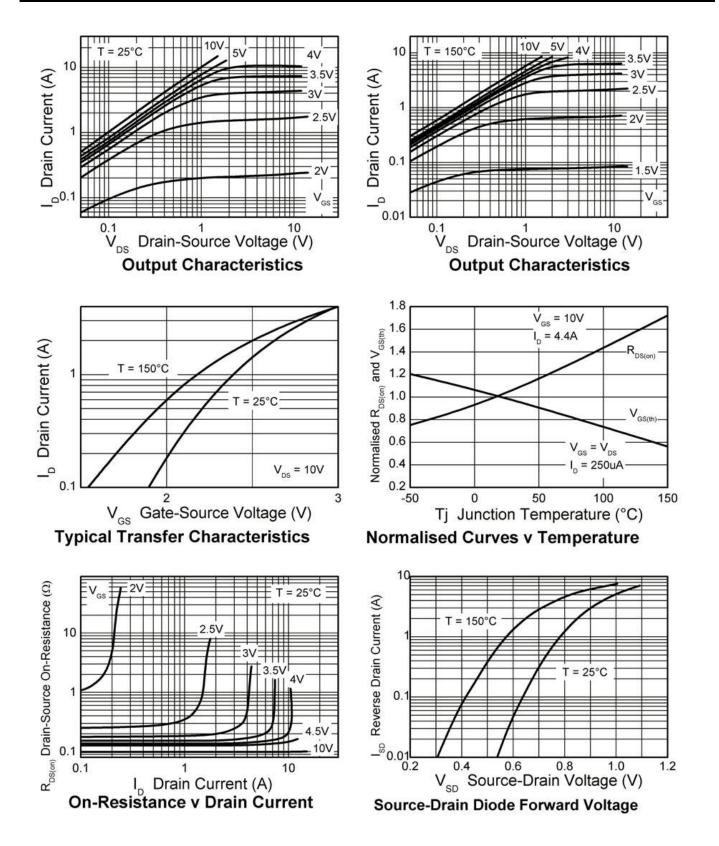
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS	0,		- 76		•		
Drain-Source Breakdown Voltage	BV _{DSS}	70	_		V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 70V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS			•		•	·	
Gate Threshold Voltage	V _{GS(th)}	1.0	—	_	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Statia Drain Source On Desistance (Nate 7)	D	_	—	0.13	Ω	$V_{GS} = 10V, I_D = 4.4A$	
Static Drain-Source On-Resistance (Note 7)	R _{DS(on)}	_	—	0.19		$V_{GS} = 4.5V, I_D = 3.8A$	
Forward Transfer Admittance	g fs	_	4.66		S	$V_{DS} = 15V, I_D = 4.4A$	
Diode Forward Voltage (Note 7)	V _{SD}	_	0.85	0.95	V	$T_J = +25^{\circ}C$, $V_{GS} = 0V$, $I_S = 2.5A$	
DYNAMIC CHARACTERISTICS (Notes 8 & 9)			•		•	·	
Input Capacitance	Ciss	_	298	_		$V_{DS} = 50V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	Coss	_	35	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	21	—			
Total Gate Charge	Qg	_	4.35	—	nC	$V_{DS} = 35V, V_{GS} = 5.0V, I_D = 4.4A$	
Total Gate Charge	Qg	_	7.4	—		$V_{DS} = 35V, V_{GS} = 10V, I_D = 4.4A$	
Gate-Source Charge	Q _{gs}	_	1.06	_	nC		
Gate-Drain Charge	Q _{gd}		1.8				
Turn-On Delay Time	t _{D(on)}	_	1.9	—		$V_{DS} = 35V, V_{GS} = 10V,$ $I_{D} = 1A, R_{G} \cong 6.0\Omega$	
Turn-On Rise Time	t _R	_	2	_			
Turn-Off Delay Time	t _{D(off)}	_	11.5	—	ns		
Turn-Off Fall Time	t _F	_	5.8	—]		
Body Diode Reverse Recovery Time	t _{RR}	_	19.8		ns	T _J = +25°C, I _S = 2.5A,	
Body Diode Reverse Recovery Charge	Q _{RR}	_	14		nC	dl/dt = 100A/µs	

7. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%. 8. Switching characteristics are independent of operating junction temperature. 9. For design aid only, not subject to production testing. Notes:

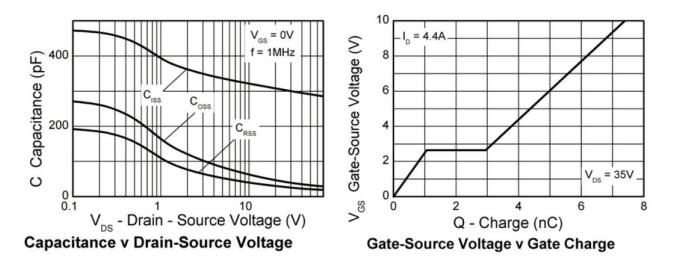


Typical Characteristics





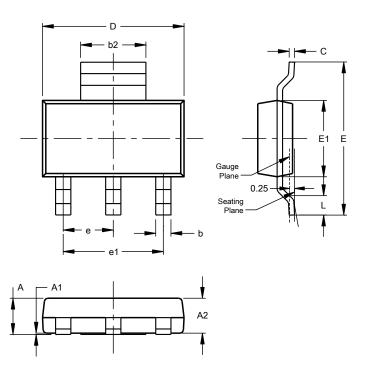
Typical Characteristics (continued)





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



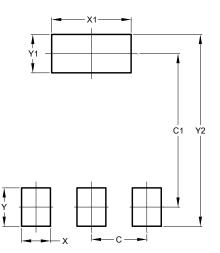
SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
Е	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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